MOTOROLA

MDA800 MDA801 MDA802 MDA804 MDA806

Designers Data Sheet

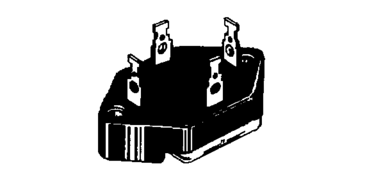
FULL WAVE BRIDGE RECTIFIER ASSEMBLIES

. . . utilizing individual MR2500 type plastic button rectifiers interconnected and then enclosed in plastic to provide a single rugged package. Devices are available with voltages from 50 to 600 Volts with these additional features.

- 1500 Volt Heat Sink Isolation
- Slip-On Terminals
- High Surge Capability
- Output Current Ratings for Both Case and Ambient Conditions

SINGLE-PHASE FULL-WAVE BRIDGE

8.0 AMPERE
50 thru 600 VOLTS



Designers Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves—representing boundaries on device characteristics—are given to facilitate "worst case" design.

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	MDA 800	MDA 801	MDA 802	MDA 804	MDA 806	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
DC Output Voltage Resistive Load Capacitive Load	Vdc	 30 50	 62 100	 124 200	 250 400	 380 600	Volts
Average Rectified Forward Current (Single phase bridge, resistive load, 60 Hz) T_A = 55°C (unmounted) T_A = 55°C (1) T_C = 100°C	I_O	← 3.5 → ← 6.0 → ← 8.0 →					Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	← 400 →					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← −65 to +175 →					°C

(1) Chassis mounted, 7" x 7" aluminum.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient — Each Die	$R_{\theta JA}$	40	°C/W
Effective Bridge	$R_{\theta JA(EFF)}$	23	°C/W
Thermal Resistance, Junction to Case — Each Die	$R_{\theta JC}$	16	°C/W
Effective Bridge	$R_{\theta JC(EFF)}$	5.6	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage, Per Diode (2) (i_F = 18.9 A) (i_F = 18.9 A, T_J = 175°C)	v_F	 0.9 —	 1.0 0.85	Volts
Reverse Current, Per Diode (Rated V_R)	I_R	—	0.5	mA

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MECHANICAL CHARACTERISTICS

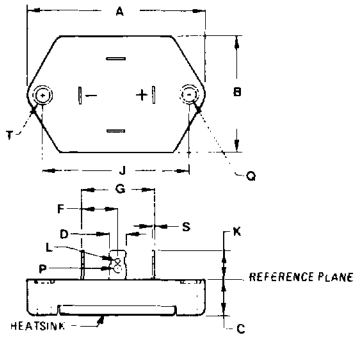
CASE: Transfer-molded plastic case with an electrically isolated aluminum base.

POLARITY: Terminal-designation embossed on case — + DC Output
− DC Output
AC not marked

MOUNTING POSITION: Any, highest heat transfer efficiency accomplished through the surface opposite the terminals. Use silicone heat sink compound for maximum heat transfer.

WEIGHT: 29 grams (approx.)

TERMINALS: Readily solderable, corrosion resistant, suitable for slip-on terminals.



NOTE
1. MOUNTING HOLES WITHIN 0.25 mm (0.010) DIA OF TRUE POSITION AT MAXIMUM MATERIAL CONDITION
2. COUNTERSUNK MOUNTING HOLES FOR 321-02 ONLY! 3 18 (0 125) DEEP.
3. DIMENSIONS F AND G SHALL BE MEASURED AT THE REFERENCE PLANE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	47 45	47 75	1 868	1.880
B	25 65	26 16	1 010	1.030
C	12.45	13.49	0 490	0.531
D	6.10	6.60	0.240	0 260
F	10.00	10.50	0 394	0.413
G	20.00	21.00	0.787	0.827
J	33.32	BSC	1.312	BSC
K	9.52	11 43	0.375	0.450
L	1.52	2.06	0.060	0.081
P	2 79	2 92	0.110	0.115
Q	3 94	4 19	0.155	0.165
S	0 71	0 85	0 028	0.034
T	7.24	7 49	0.285	0.295

CASE 321-02

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FIGURE 1 – FORWARD VOLTAGE

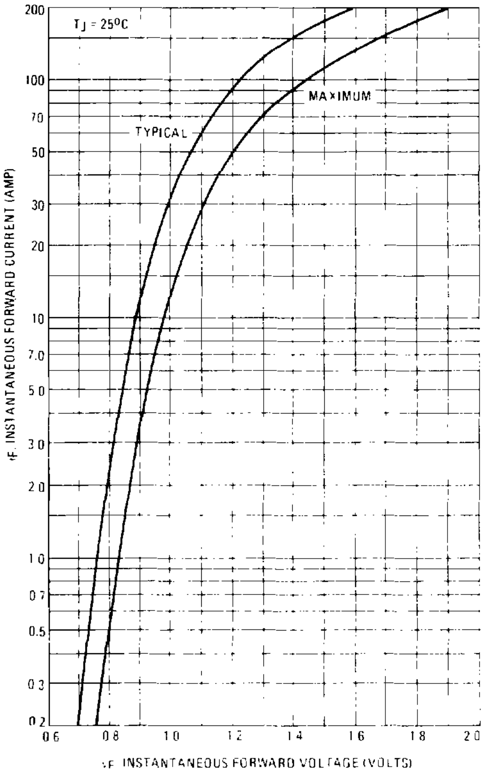


FIGURE 2 – NON-REPETITIVE SURGE CURRENT

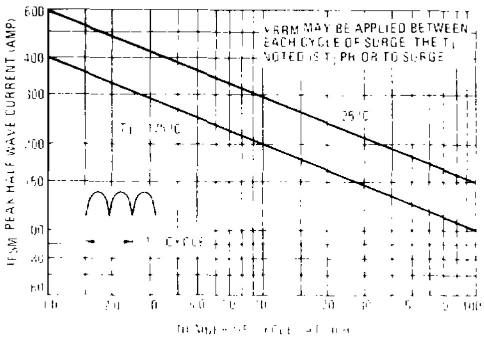


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

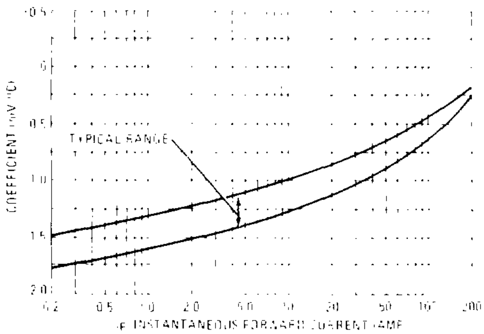
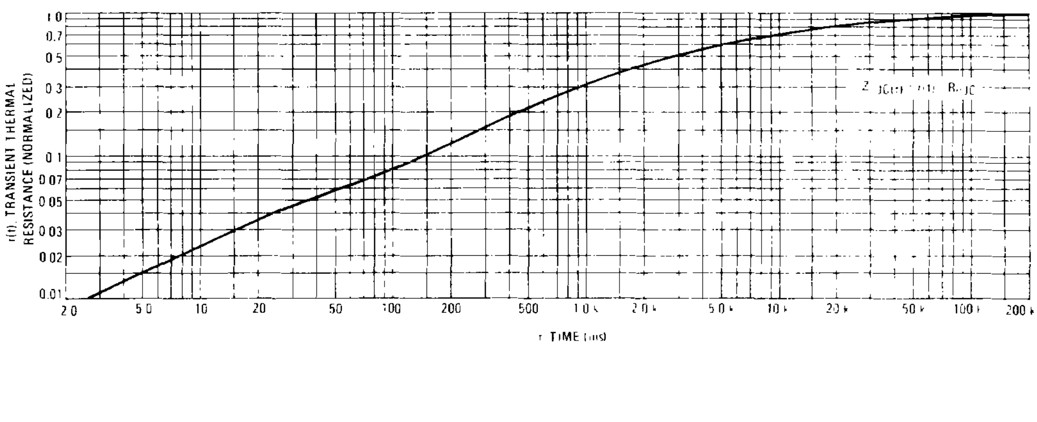


FIGURE 4 – TYPICAL THERMAL RESPONSE



MAXIMUM CURRENT RATINGS, BRIDGE OPERATION

FIGURE 5 – AMBIENT TEMPERATURE DERATING

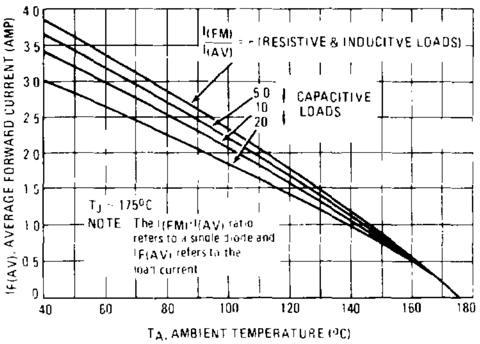
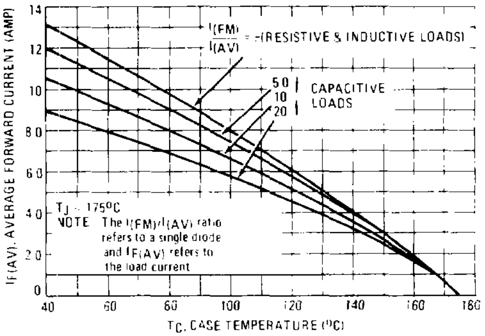


FIGURE 6 – CASE TEMPERATURE DERATING



TYPICAL DYNAMIC CHARACTERISTICS (EACH DIODE)

FIGURE 7 – RECTIFICATION WAVEFORM EFFICIENCY

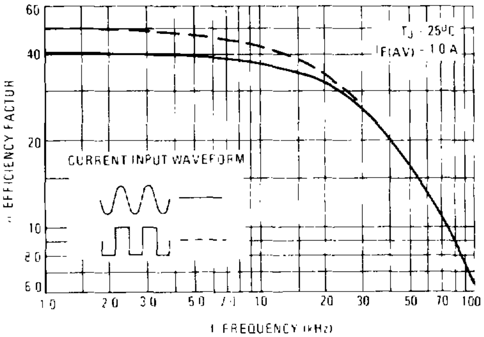


FIGURE 8 – CAPACITANCE

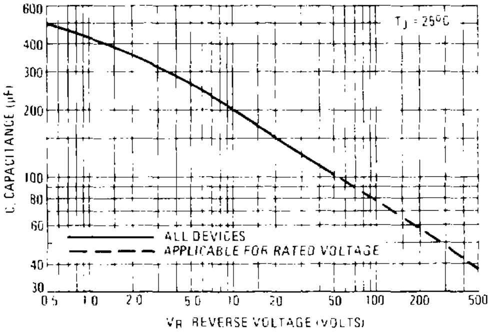


FIGURE 9 – REVERSE RECOVERY TIME

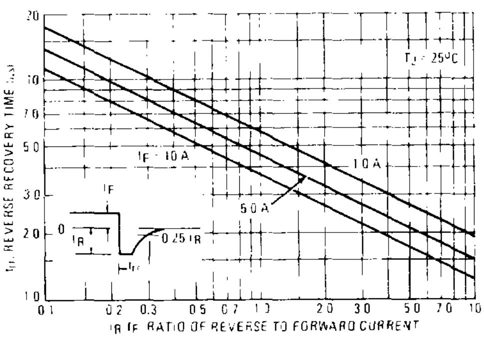


FIGURE 10 – FORWARD RECOVERY TIME

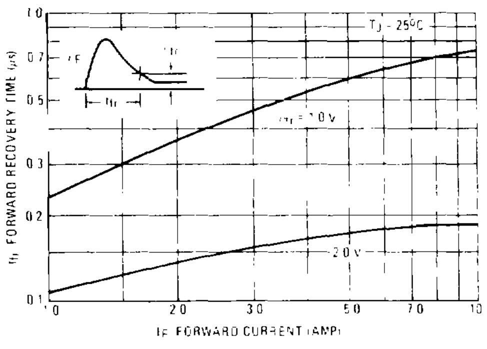
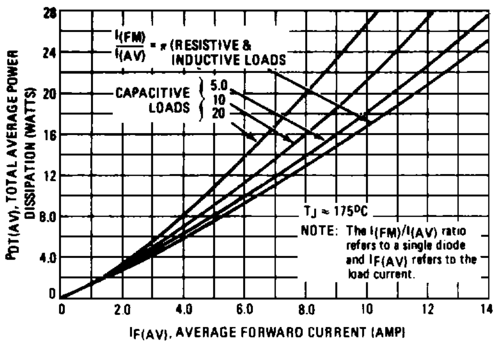


FIGURE 11 – POWER DISSIPATION FIGURE



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NOTE 1 – THERMAL COUPLING AND EFFECTIVE THERMAL RESISTANCE

In multiple chip devices where there is coupling of heat between die, the junction temperature can be calculated as follows:

(1) $\Delta T_{J1} = R_{\theta 1} P_{D2} + R_{\theta 2} K_{\theta 2} P_{D2} + R_{\theta 3} K_{\theta 3} P_{D3} + R_{\theta 4} K_{\theta 4} P_{D4}$

Where ΔT_{J1} is the change in junction temperature of diode 1

$R_{\theta 1}$ thru 4 is the thermal resistance of diodes 1 through 4.

P_{D1} thru 4 is the power dissipated in diodes 1 through 4

$K_{\theta 2}$ thru 4 is the thermal coupling between diode 1 and diodes 2 through 4

An effective package thermal resistance can be defined as follows

(2) $R_{\theta(EFF)} = \Delta T_{J1}/P_{DT}$

Where: P_{DT} is the total package power dissipation.

Assuming equal thermal resistance for each die, equation (1) simplifies to

(3) $\Delta T_{J1} = R_{\theta 1}(P_{D1} + K_{\theta 2} P_{D2} + K_{\theta 3} P_{D3} + K_{\theta 4} P_{D4})$

For the condition where $P_{D1} = P_{D2} = P_{D3} = P_{D4}$, $P_{DT} = 4P_{D1}$ equation (3) can be further simplified and by substituting into equation (2) results in

(4) $R_{\theta(EFF)} = R_{\theta 1}\ (1 + K_{\theta 2} + K_{\theta 3} + K_{\theta 4})/4$

For the MDA800 rectifier assembly, thermal coupling between opposite diodes is 10% and between adjacent diodes is 15% when the case temperature is used as a reference. Similarly for ambient mounting thermal coupling between opposite diodes is 40% and between adjacent diodes is 45%.

NOTE 2 – SPLIT LOAD DERATING INFORMATION

Bridge rectifiers are used in two basic configurations as shown in circuits A and B of Figure 12. The current derating data of Figures 5 and 6 apply to the standard bridge circuit (A) where $I_A = I_B$. For circuit B where $I_A \neq I_B$, derating information can be calculated as follows:

(5) $T_{R(MAX)} = T_{J(MAX)} - \Delta T_{J1}$

Where $T_{R(MAX)}$ is the reference temperature (either case or ambient)

ΔT_{J1} can be calculated using equation (3) in Note 1

For example, to determine $T_{C(MAX)}$ for the MDA800 with the following capacitive load conditions:

I_A = 10 A average with a peak of 46 A

I_B = 5.0 A average with a peak of 35 A

First calculate the peak to average ratio for I_A. $I_{(FM)}/I_{(AV)}$ = 46/5.0 = 9.2 (Note that the peak to average ratio is on a per diode basis and each diode provides 5.0 A average).

From Figure 11, for an average current of 10 A and an $I_{(FM)}/I_{(AV)}$ = 9.2 read $P_{DT(AV)}$ = 21 watts or 5.25 watts/diode. Thus $P_{D1} = P_{D3}$ = 5.25 watts.

Similarly, for a load current I_B of 5.0 A, diode #2 and diode #4 each see 2.5 A average resulting in an $I_{(FM)}/I_{(AV)}$ = 14.

Thus, the package power dissipation for 5.0 A is 10 watts or 2.5 watts/ diode. $\therefore P_{D2} = P_{D4}$ = 2.5 watts.

The maximum junction temperature occurs in diodes #1 and #3. From equation (3) for diode #1 ΔT_{J1} = 16 [5.25 + 0.1 (2.5) + 0.15 (5.25) + 0.15 (2.5)]

$\Delta T_{J1} \approx 106°C$

Thus $T_{C(MAX)} = 175 - 106 = 69°C$

The total package dissipation in this example is:

$P_{DT} = 2 \times 5.25 + 2 \times 2.5 = 15.5$ watts.

FIGURE 12 – BASIC CIRCUIT USES FOR BRIDGE RECTIFIERS